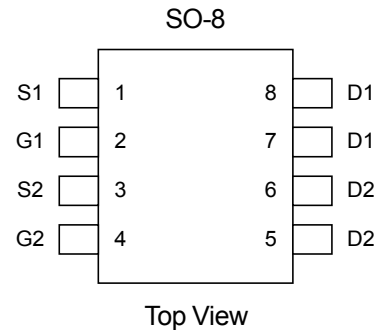


N-Channel Enhancement Mode MOSFET

Features

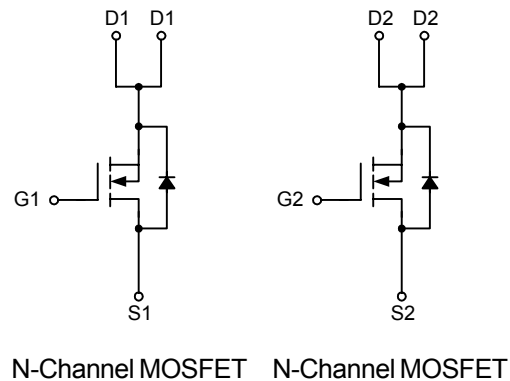
- 30V/6A , $R_{DS(ON)} = 21m\Omega (typ.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 32m\Omega (typ.) @ V_{GS} = 5V$
- Super High Dense Cell Design for Extremely Low $R_{DS(ON)}$
- Reliable and Rugged
- SO-8 Package

Pin Description



Applications

- Power Management in Notebook Computer , Portable Equipment and Battery Powered Systems.



Ordering and Marking Information

APM7314 □□-□□ Handling Code Temp. Range Package Code	Package Code K : SO-8 Temp. Range C : 0 to 70°C Handling Code TR : Tape & Reel
APM7314 K : APM7314 XXXXX	XXXXX - Date Code

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
I _D [*]	Maximum Drain Current – Continuous		6	A
I _{DM}	Maximum Drain Current – Pulsed		24	
P _D	Maximum Power Dissipation	T _A =25°C	1.6	W
		T _A =100°C	0.625	W
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
R _{θJA}	Thermal Resistance – Junction to Ambient		80	°C/W

* Surface Mounted on FR4 Board, $t \leq 10$ sec.

Electrical Characteristics ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM7314			Unit
			Min.	Typ.	Max.	
Static						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _{DS} =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V , V _{GS} =0V			1	μA
		V _{DS} =24V, V _{GS} =0V, T _j = 55°C			5	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1		3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V , I _{DS} =3.5A		21	24	mΩ
		V _{GS} =5V , I _{DS} =2A		32	35	
V _{SD} ^a	Diode Forward Voltage	I _{SD} =2A , V _{GS} =0V	0.6		1.1	V

Electrical Characteristics Cont. (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	APM7314			Unit
			Min.	Typ.	Max.	
Dynamic ^b						
Q _g	Total Gate Charge	V _{DS} =15V , I _{DS} = 10A V _{GS} =5V ,		15	20	nC
Q _{gs}	Gate-Source Charge			5.8		
Q _{gd}	Gate-Drain Charge			3.8		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V , I _{DS} =2A , V _{GEN} =10V , R _G =6Ω		11	18	ns
T _r	Turn-on Rise Time			17	26	
t _{d(OFF)}	Turn-off Delay Time			37	54	
T _f	Turn-off Fall Time			20	30	
C _{iss}	Input Capacitance	V _{GS} =0V		1200		pF
C _{oss}	Output Capacitance	V _{DS} =15V		220		
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz		100		

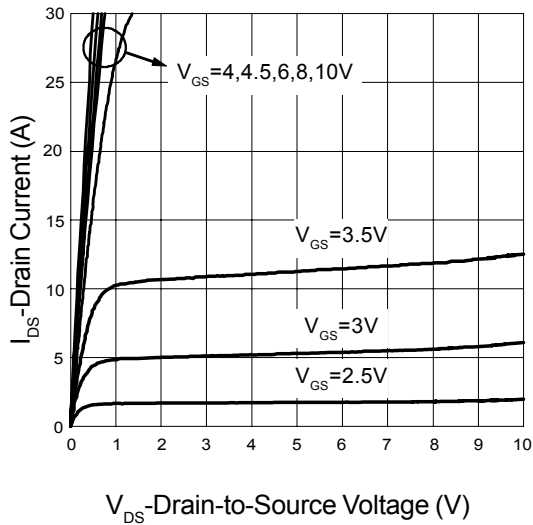
Notes

^a : Pulse test ; pulse width ≤300μs, duty cycle ≤ 2%

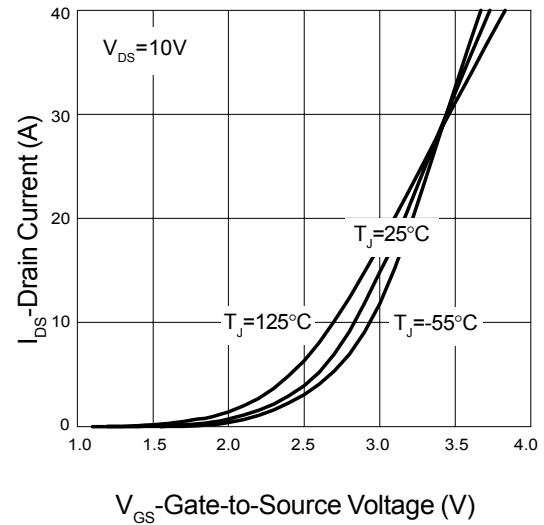
^b : Guaranteed by design, not subject to production testing

Typical Characteristics

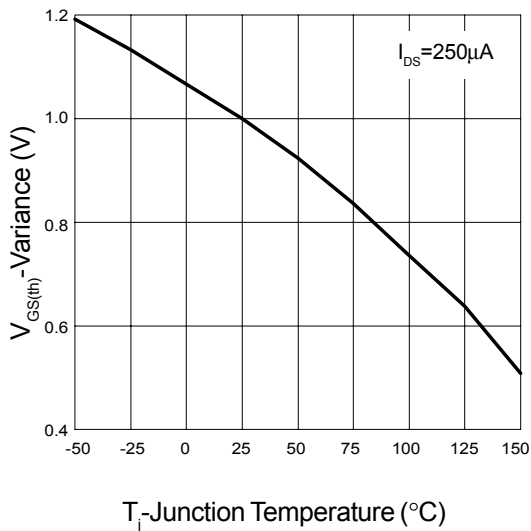
Output Characteristics



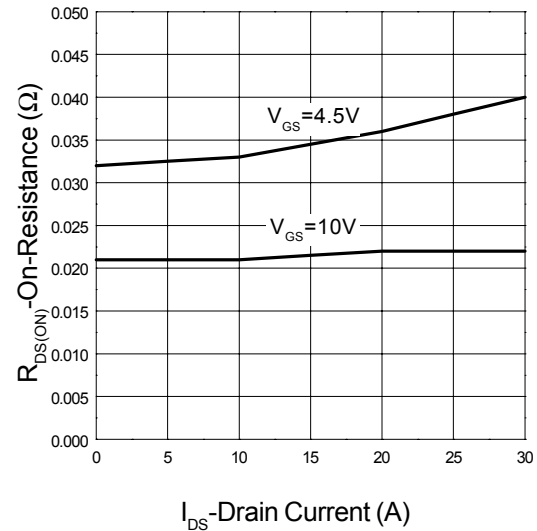
Transfer Characteristics



Threshold Voltage vs. Junction Temperature

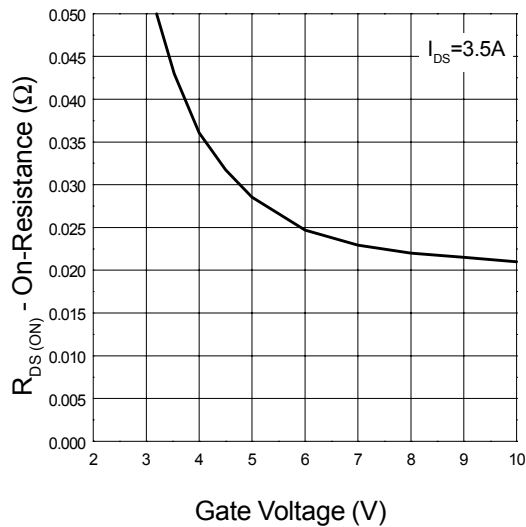


On-Resistance vs. Drain Current

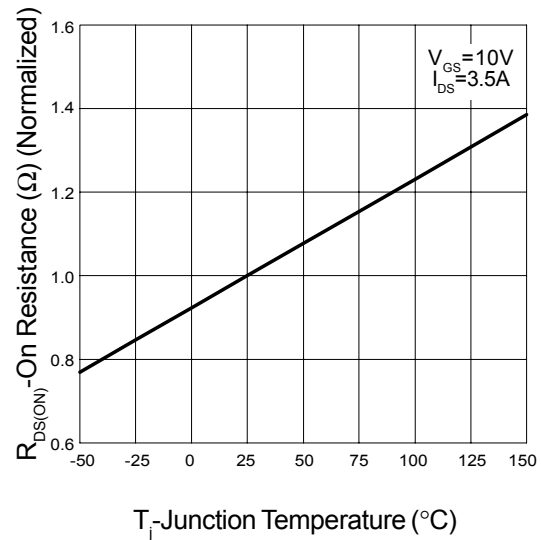


Typical Characteristics Cont.

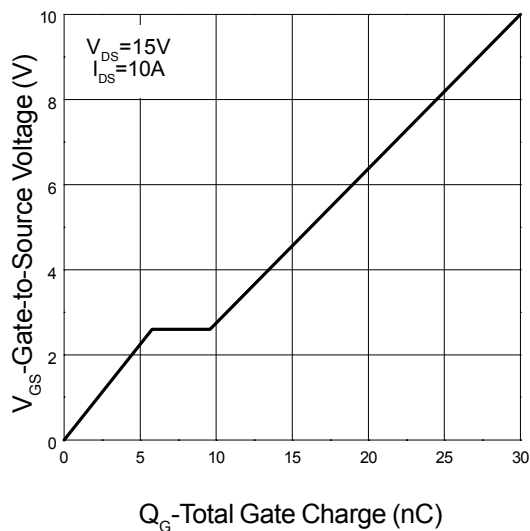
On-Resistance vs. Gate-to-Source Voltage



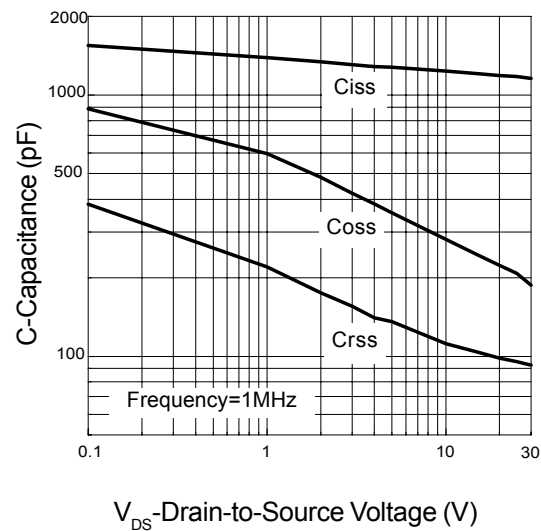
On-Resistance vs. Junction Temperature



Gate Charge

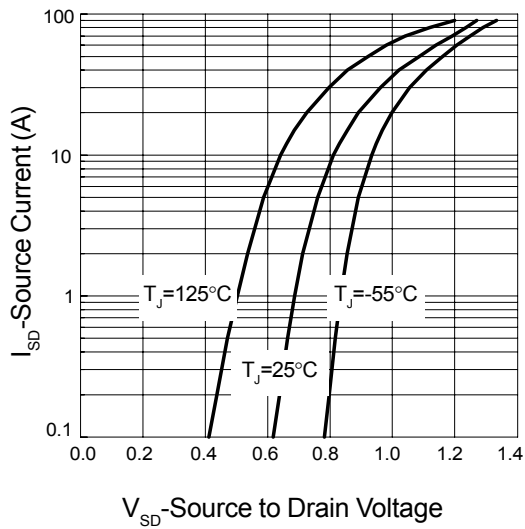


Capacitance Characteristics

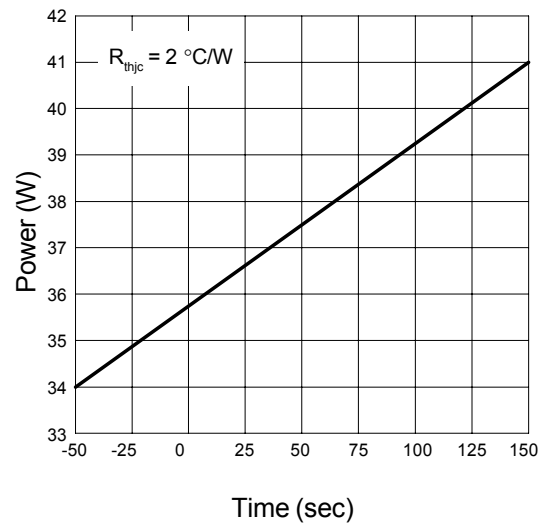


Typical Characteristics Cont.

Source-Drain Diode Forward Voltage

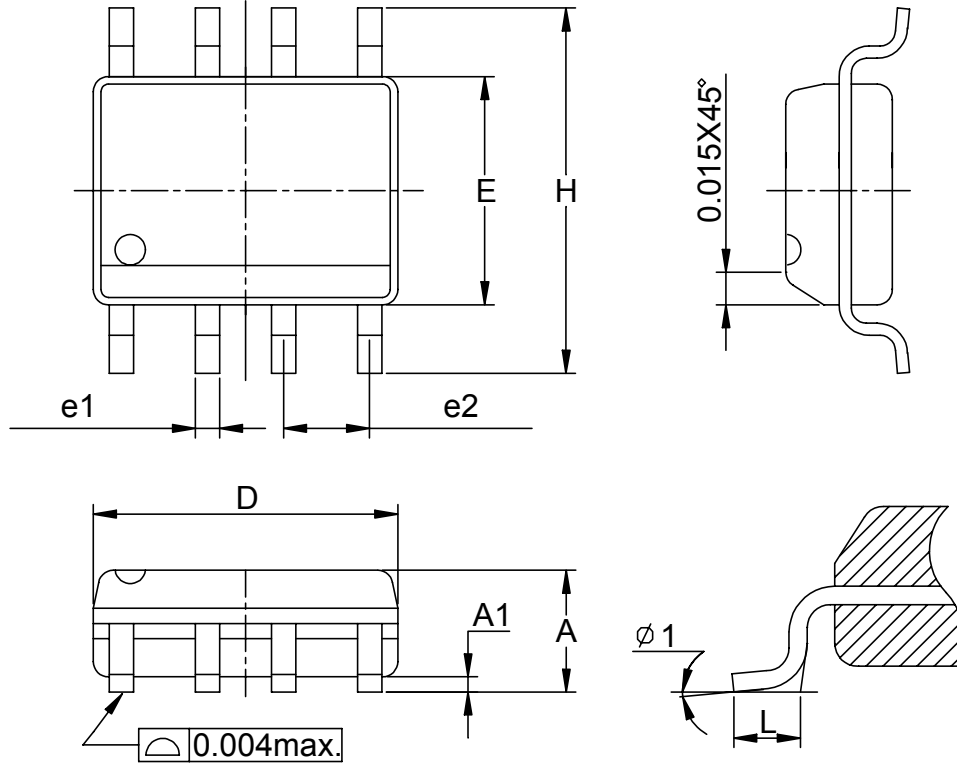


Single Pulse Power



Packaging Information

SOP-8 pin (Reference JEDEC Registration MS-012)



Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	5.00	0.189	0.197
E	3.80	4.00	0.150	0.157
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
e1	0.33	0.51	0.013	0.020
e2	1.27BSC		0.50BSC	
$\phi 1$	8°		8°	

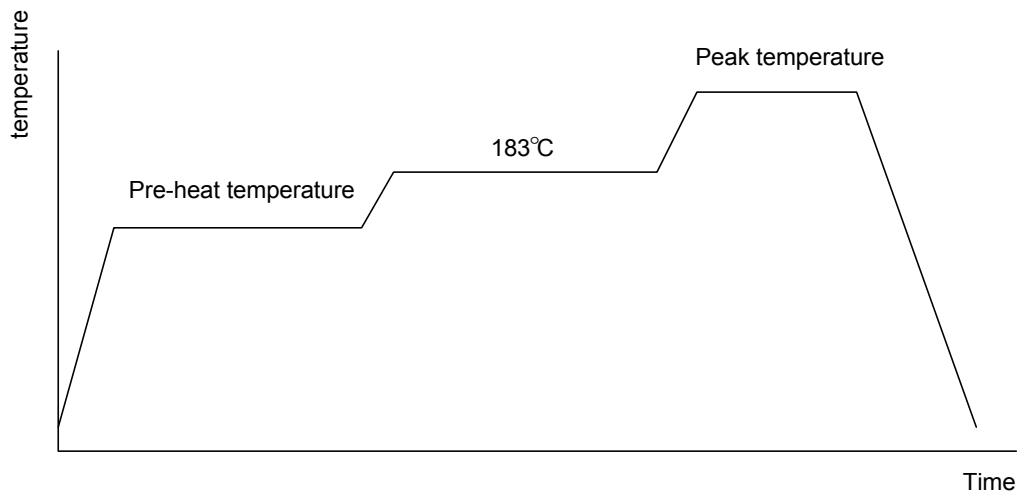
Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb)
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.
Packaging	2500 devices per reel

Reflow Condition (IR/Convection or VPR Reflow)

Reference JEDEC Standard J-STD-020A APRIL 1999

www.DataSheet4U.com



Classification Reflow Profiles

	Convection or IR/ Convection	VPR
Average ramp-up rate(183°C to Peak)	3°C/second max.	10 °C /second max.
Preheat temperature 125 ± 25°C)	120 seconds max	
Temperature maintained above 183°C	60 – 150 seconds	
Time within 5°C of actual peak temperature	10 –20 seconds	60 seconds
Peak temperature range	220 +5/-0°C or 235 +5/-0°C	215-219°C or 235 +5/-0°C
Ramp-down rate	6 °C /second max.	10 °C /second max.
Time 25°C to peak temperature	6 minutes max.	

Package Reflow Conditions

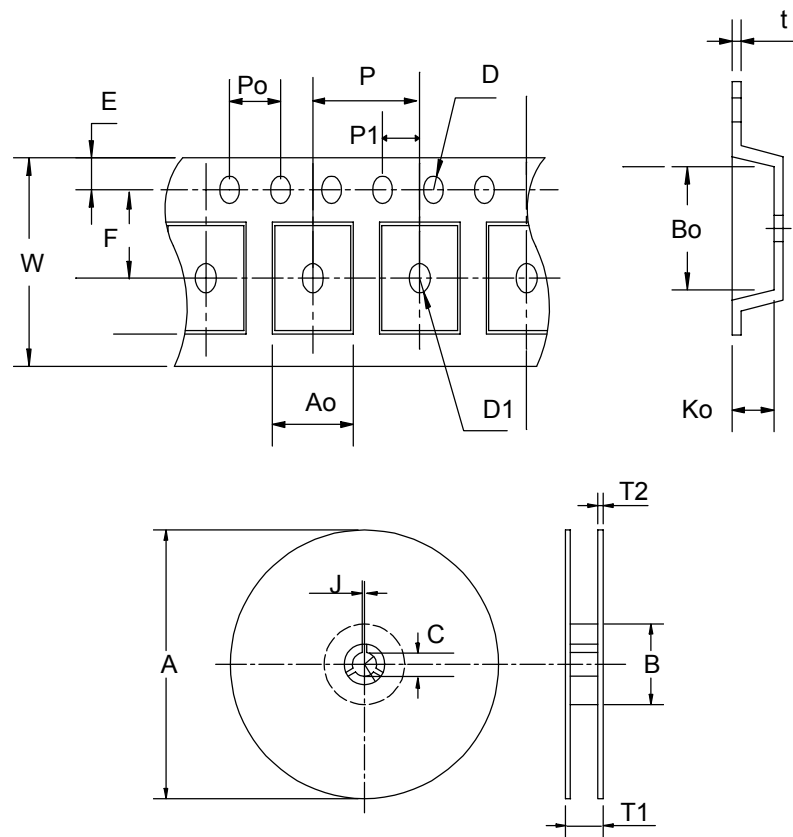
pkg. thickness ≥ 2.5mm and all bgas	pkg. thickness < 2.5mm and pkg. volume ≥ 350 mm ³	pkg. thickness < 2.5mm and pkg. volume < 350mm ³
Convection 220 +5/-0 °C		Convection 235 +5/-0 °C
VPR 215-219 °C		VPR 235 +5/-0 °C
IR/Convection 220 +5/-0 °C		IR/Convection 235 +5/-0 °C

Reliability test program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

www.DataSheet4U.com

Carrier Tape & Reel Dimensions



Application	A	B	C	J	T1	T2	W	P	E
SOP-8	330±1	62 ± 1.5	12.75 + 0.15	2 + 0.5	12.4 +0.2	2± 0.2	12 + 0.3 - 0.1	8± 0.1	1.75± 0.1
Application	F	D	D1	Po	P1	Ao	Bo	Ko	t
SOP-8	5.5 ± 0.1	1.55±0.1	1.55+ 0.25	4.0 ± 0.1	2.0 ± 0.1	6.4 ± 0.1	5.2± 0.1	2.1± 0.1	0.3±0.013

(mm)

Cover Tape Dimensions

Carrier Width	12
Cover Tape Width	9.3

(mm)

Customer Service**Anpec Electronics Corp.**

Head Office :

5F, No. 2 Li-Hsin Road, SBIP,

Hsin-Chu, Taiwan, R.O.C.

Tel : 886-3-5642000

Fax : 886-3-5642050

Taipei Branch :

7F, No. 137, Lane 235, Pac Chiao Rd.,

Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.

Tel : 886-2-89191368

Fax : 886-2-89191369